1N5711, 1N5712, 5082-2800 Series

Schottky Barrier Diodes for General Purpose Applications



Data Sheet

Description/Applications

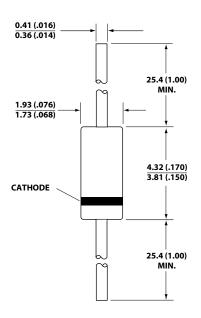
The 1N5711, 1N5712, 5082-2800/10/11 are passivated Schottky barrier diodes which use a patented "guard ring" design to achieve a high breakdown voltage. Packaged in a low cost glass package, they are well suited for high level detecting, mixing, switching, gating, log or A-D converting, video detecting, frequency discriminating, sampling, and wave shaping.

The 5082-2835 is a passivated Schottky diode in a low cost glass package. It is optimized for low turn-on voltage. The 5082-2835 is particularly well suited for the UHF mixing needs of the CATV marketplace.

Features

- Low Turn-On Voltage As Low as 0.34 V at 1 mA
- Pico Second Switching Speed
- High Breakdown Voltage Up to 70 V
- Matched Characteristics Available

Outline 15



DIMENSIONS IN MILLIMETERS AND (INCHES).

Maximum Ratings

-	
Junction Operating and Storage Tempe	erature Range
1N5711, 1N5712, 5082-2800/10/11	65°C to +200°C
5082-2835	60°C to +150°C
DC Power Dissipation	
(Measured in an infinite heat sink at T	$_{CASE} = 25^{\circ}C$
Derate linearly to zero at maximum ra	ted temp.
1N5711, 1N5712, 5082-2800/10/11	250 mW
5082-2835	150 mW
Peak Inverse Voltage	V _{BR}

Package Characteristics

	Outline 15
Lead Material	Dumet
Lead Finish	95-5% Tin-Lead
Max. Soldering Temperature	260°C for 5 sec
Min. Lead Strength	4 pounds pull
Typical Package Inductance	
1N5711, 1N5712:	2.0 nH
2800 Series:	2.0 nH
Typical Package Capacitance	
1N5711, 1N5712:	0.2 pF
2800 Series:	0.2 pF

The leads on the Outline 15 package should be restricted so that the bend starts at least 1/16 inch from the glass body. Outline 15 diodes are available on tape and reel. The tape and reel specification is patterned after RS-296-D.

Electrical Specifications at $T_A = 25$ °C

General Purpose Diodes

Part Number	Package Outline	Min. Breakdown Voltage V _{BR} (V)	Max. Forward Voltage V _F (mV)	$V_F = 1 \text{ V Max.}$ at Forward Current I_F (mA)	Ma Reverse I Curr I _R (nA) a	Leakage ent	Max. Capacitance C _T (pF)
5082-2800	15	70	410	15	200	50	2.0
1N5711	15	70	410	15	200	50	2.0
5082-2810	15	20	410	35	100	15	1.2
1N5712	15	20	550	35	150	16	1.2
5082-2811	15	15	410	20	100	8	1.2
5082-2835	15	8*	340	10*	100	1	1.0
Test Conditions		I _R = 10 μΑ *I _R = 100 μΑ	$I_F = 1 \text{ mA}$	$^*V_F = 0.45 \text{ V}$			$V_R = 0 V$ f = 1.0 MHz

Note: Effective Carrier Lifetime (τ) for all these diodes is 100 ps maximum measured with Krakauer method at 5 mA except for 5082-2835 which is measured at 20 mA.

Matched Pairs and Quads

Basic Part Number 5082-	Matched Pair Unconnected	Matched Quad Unconnected	Batch Matched ^[1]	Test Conditions
2800	5082-2804 $\Delta V_{F} = 20 \text{ mV}$	5082-2805 $\Delta V_{F} = 20 \text{ mV}$		ΔV_F at $I_F = 0.5, 5 \text{ m}$. $*I_F = 10 \text{ mA}$ ΔC_O at $f = 1.0 \text{ MHz}$
2811			5082-2826 $\Delta V_F = 10 \text{ mV}$ $\Delta C_O = 0.1 \text{ pF}$	ΔV_F at $I_F = 10 \text{ mA}$ ΔC_O at $f = 1.0 \text{ MH}$
2835			5082-2080 $\Delta V_F = 10 \text{ mV}$ $\Delta C_O = 0.1 \text{ pF}$	ΔV_F at $I_F = 10 \text{ mA}$ ΔC_O at $f = 1.0 \text{ MH}$

Note:

SPICE Parameters

Parameter	Units	5082-2800	5082-2810	5082-2811	5082-2835
B_V	V	75	25	18	9
C_{J0}	рF	1.6	0.8	1.0	0.7
E_{G}	eV	0.69	0.69	0.69	0.69
I _{BV}	Α	10E-5	10E-5	10E-5	10E-5
I _s	Α	2.2 x 10E ⁻⁹	1.1 x 10E ⁻⁹	0.3 x 10E ⁻⁸	2.2 x 10E ⁻⁸
N		1.08	1.08	1.08	1.08
R_s	Ω	25	10	10	5
$P_{_{B}}$	V	0.6	0.6	0.6	0.56
P _T		2	2	2	2
M		0.5	0.5	0.5	0.5

^{1.} Batch matched devices have a minimum batch size of 50 devices.

Typical Parameters

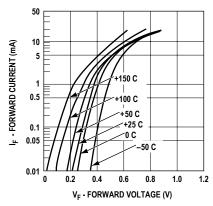


Figure 1. I-V Curve Showing Typical Temperature Variation for 5082-2800 or 1N5711 Schottky Diodes.

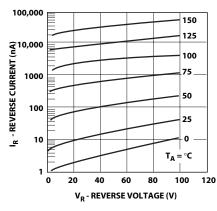


Figure 2. (5082-2800 OR 1N5711) Typical Variation of Reverse Current (I_R) vs. Reverse Voltage (V_R) at Various Temperatures.

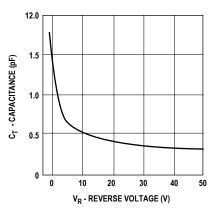


Figure 3. (5082-2800 or 1N5711) Typical Capacitance (C_T) vs. Reverse Voltage (V_R).

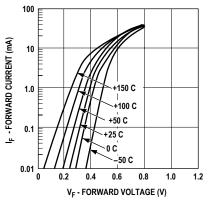


Figure 4. I-V Curve Showing Typical Temperature Variation for the 5082-2810 or 1N5712 Schottky Diode.

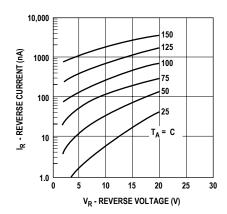


Figure 5. (5082-2810 or 1N5712) Typical Variation of Reverse Current (I_R) vs. Reverse Voltage (V_R) at Various Temperatures.

Notes:

Typical values were derived using limited samples during initial product characterization and may not be representative of the overall distribution

Typical Parameters, continued

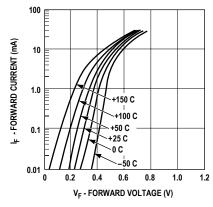


Figure 6. I-V Curve Showing Typical Temperature Variation for the 5082-2811 Schottky Diode.

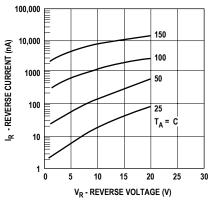


Figure 7. (5082-2811) Typical Variation of Reverse Current (I_R) vs. Reverse Voltage (V_R) at Various Temperatures.

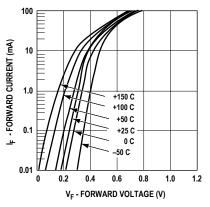


Figure 8. I-V Curve Showing Typical Temperature Variations for 5082-2835 Schottky Diode.

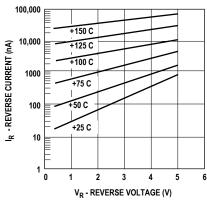


Figure 9. (5082-2835) Typical Variation of Reverse Current (I $_R$) vs. Reverse Voltage (V $_R$) at Various Temperatures.

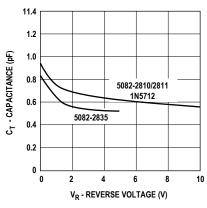


Figure 10. Typical Capacitance (C_T) vs. Reverse Voltage (V_R).

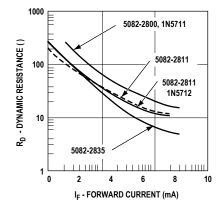


Figure 11. Typical Dynamic Resistance (R_D) vs. Forward Current (I_F).

Notes

Typical values were derived using limited samples during initial product characterization and may not be representative of the overall distribution

Tape Dimensions and Product Orientation

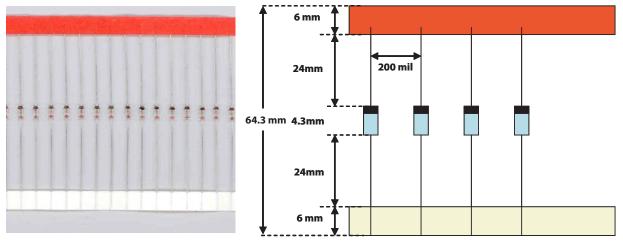


Figure 13.

RFD Reel Dimensions for T25/T50

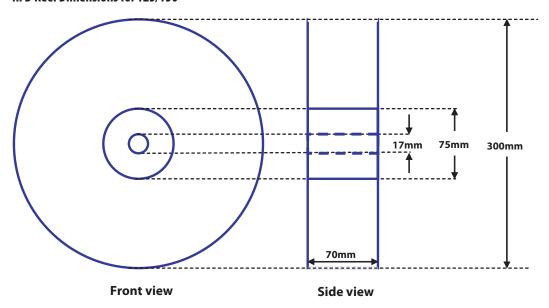


Figure 14.

Diode Package Marking

1N5xxx 5082-xxxx

would be marked:

1Nx xx
xxx xx
YWW YWW

where xxxx are the last four digits of the 1Nxxxx or the 5082-xxxx part number. Y is the last digit of the calendar year. WW is the work week of manufacture.

Examples of diodes manufactured during workweek 45 of 1999:

1N5712 5082-3080

would be marked:

1N5 30 712 80 945 945

Part Number Ordering Information

Part Number	No. of devices	Container	
5082-28xx#T25/1N57xx#T25	2500	Tape & Reel	
5082-28xx#T50/ 1N57xx#T50	5000	Tape & Reel	
5082-28xx/ 1N57xx	100	Antistatic bag	

